

# Silicon Solid State Devices and Radiation Detection

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 World Scientific

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 **World Scientific**

NEW JERSEY • LONDON • SINGAPORE • BEIJING • SHANGHAI • HONG KONG • TAIPEI • CHENNAI

*Published by*

World Scientific Publishing Co. Pte. Ltd.

5 Toh Tuck Link, Singapore 596224

*USA office:* 27 Warren Street, Suite 401-402, Hackensack, NJ 07601

*UK office:* 57 Shelton Street, Covent Garden, London WC2H 9HE

**British Library Cataloguing-in-Publication Data**

A catalogue record for this book is available from the British Library.

**SILICON SOLID STATE DEVICES AND RADIATION DETECTION**

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ISBN 978-981-4390-04-0

Printed by FuIsland Offset Printing (S) Pte Ltd Singapore

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